

DZ2412000L

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

Capability of withstanding a high surge type

DZ2W120 in Power type package

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: RJ

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	500	mA
Forward current	IF	400	mA
Total power dissipation ^{*1}	PT	2	W
Non-repetitive reverse power surge ^{*2}	PZSM	100	W
Electrostatic discharge ^{*3}	ESD	±30	kV
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note: *1 Mounted on ceramics print circuit board.

Board size: 50 mm × 50 mm

Board thickness: 0.8 mm

Soldering size: 2 mm × 2 mm

*2 $t = 0.1\text{ms}$

*3 Test method: IEC61000_4_2(C = 150 pF, R = 330 Ω, Contact discharge: 10 times)

■ Electrical Characteristics $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	IF = 200 mA			1.2	V
Zener voltage ^{*1, *2}	V _Z	IZ = 10 mA	11.40	12.00	12.60	V
Zener operating resistance	R _Z	IZ = 10 mA			30	Ω
Reverse current	IR	VR = 8.0 V			10	μA
Temperature coefficient of zener voltage ^{*3}	SZ	IZ = 10 mA		8.8		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

3. *1 The temperature must be controlled 25°C for V_Z measurement.

V_Z value measured at other temperature must be adjusted to V_Z (25°C)

*2 V_Z guaranteed 20 ms after current flow.

*3 T_j = 25°C to 150°C

